On page 6, paragraph beginning on line 9:

In detail, the thin film transistor has a laminated film structure and includes a gate electrode 202a connected to the gate line 202, a gate insulation film 203, which is made of silicon nitride (SiN_x), formed on the entire surface including the gate line 202, an semiconductor layer 204 made of amorphous silicon, and source/drain electrodes 205a and 205b connected to the data line 205. A reflective electrode 207a, which will be formed later, is electrically connected with the drain electrode through a pixel contact hole 208 formed by removing the first passivation film on the drain electrode 205b. As a result, a voltage according to the on-off action of the thin film transistor is applied to the reflective electrode 207a.

On page 12, paragraph beginning on line 10:

At this time, the capacitor lower electrode 302c, the gate insulation film 303 and the capacitor upper electrode 305c form a storage capacitor. A laminated structure consisting of the gate electrode 302a, the gate insulation film 303, a semiconductor layer 304 and the source/drain electrodes 305a and 305b forms a thin film transistor. An a-Si:H TFT (amorphous Silicon Thin Film Transistor) having the semiconductor layer 304 made of amorphous silicon is the main current.

In the Claims

Please amend the claims as follows:

1. (Amended) A reflective liquid crystal display device comprising:

a plurality of gate lines and data lines intersecting on a first substrate, the gate lines and the data lines defining pixel areas;

a plurality of thin film transistors formed at the intersections of the gate lines and the data lines, each thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

a capacitor lower electrode of a storage capacitor formed on the same plane as a gate line;